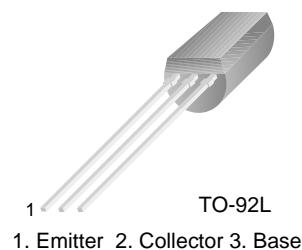


■■ APPLICATION: High Voltage General Amplifier Applications.

■■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	200	V
Collector-emitter voltage	V_{CEO}	160	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_c	0.1	A
Collector Power Dissipation	P_c	0.8	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^\circ\text{C}$


■■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	120		400		$V_{CE}=10\text{V}$, $I_c=10\text{mA}$
Collector Cut-off Current	I_{CBO}			0.1	μA	$V_{CB}=200\text{V}$, $I_E=0$
Emitter Cut-off Current	I_{EBO}			0.1	μA	$V_{EB}=5\text{V}$, $I_c=0$
Collector-Base Breakdown Voltage	BV_{CBO}	200			V	$I_c=0.05\text{mA}$, $I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	160			V	$I_c=1\text{mA}$, $I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_E=0.05\text{mA}$, $I_c=0$
Base-Emitter Voltage	V_{BE}		0.6	0.7	V	$V_{CE}=10\text{V}$, $I_c=1\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	$I_c=50\text{mA}$, $I_B=5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.0	V	$I_c=50\text{mA}$, $I_B=5\text{mA}$
Gain bandwidth product	f_t	50			MHz	$I_c=10\text{mA}$, $V_{CE}=10\text{V}$
Common Base Output Capacitance	C_{ob}			7	PF	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$

■■ h_{FE} Classification And Marking

Classification	Y	GR
h_{FE}	120~240	200~400